

## P-Channel 30-V (D-S) MOSFET

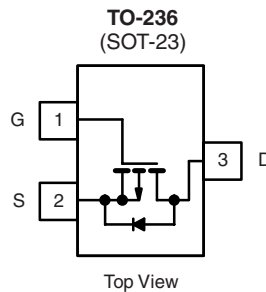
PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>b</sup>
- 30	0.078 at $V_{GS} = - 10$ V	- 3.2
	0.130 at $V_{GS} = - 4.5$ V	- 2.5

### FEATURES

- Halogen-free Option Available
- TrenchFET<sup>®</sup> Power MOSFET



**RoHS**  
COMPLIANT



Si2307BDS (L7)\*  
\* Marking Code

Ordering Information: Si2307BDS-T1-E3 (Lead (Pb)-free)  
Si2307BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	- 30		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>b</sup>	$I_D$	$T_A = 25$ °C	- 3.2	- 2.5	A
		$T_A = 70$ °C	- 2.6	- 2.0	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	- 12			
Continuous Source Current (Diode Conduction) <sup>b</sup>	$I_S$	- 1.25	- 0.75		
Power Dissipation <sup>b</sup>	$P_D$	$T_A = 25$ °C	1.25	0.75	W
		$T_A = 70$ °C	0.8	0.48	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	80	100	°C/W
Maximum Junction-to-Ambient <sup>c</sup>		130	166	

Notes:

- Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 board,  $t \leq 5$  s.
- Surface Mounted on FR4 board.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A}$	- 30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1.0		- 3.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -10\text{ V}, V_{GS} = -10\text{ V}$	- 6			A
Drain-Source On-Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3.2\text{ A}$		0.063	0.078	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$		0.105	0.130	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}, I_D = -3.2\text{ A}$		5.0		S
Diode Forward Voltage	$V_{SD}$	$I_S = -0.75\text{ A}, V_{GS} = 0\text{ V}$		- 0.85	- 1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}$ $I_D \cong -1.7\text{ A}$		9.0	15	nC
Gate-Source Charge	$Q_{gs}$			1.4		
Gate-Drain Charge	$Q_{gd}$			2.4		
Gate Resistance	$R_g$	$f = 1.0\text{ MHz}$		8.0		$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		380		$\mu\text{F}$
Output Capacitance	$C_{oss}$			100		
Reverse Transfer Capacitance	$C_{rss}$			75		
<b>Switching<sup>c</sup></b>						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -4.5\text{ V}$ $R_g = 6\text{ }\Omega$		9	20	ns
	$t_r$			12	20	
Turn-Off Time	$t_{d(off)}$			25	40	
	$t_f$			14	21	

## Notes:

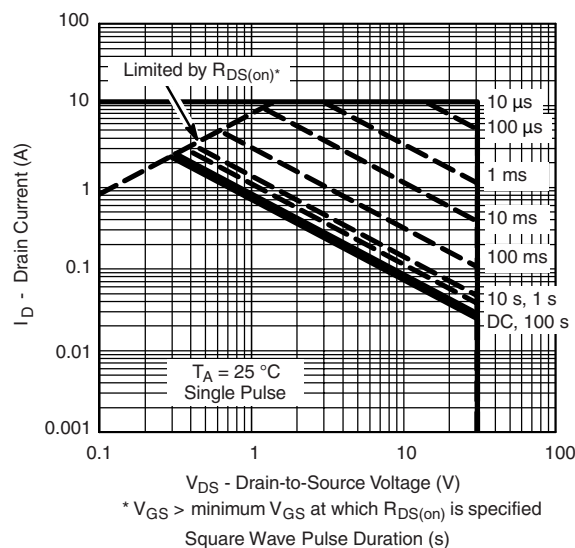
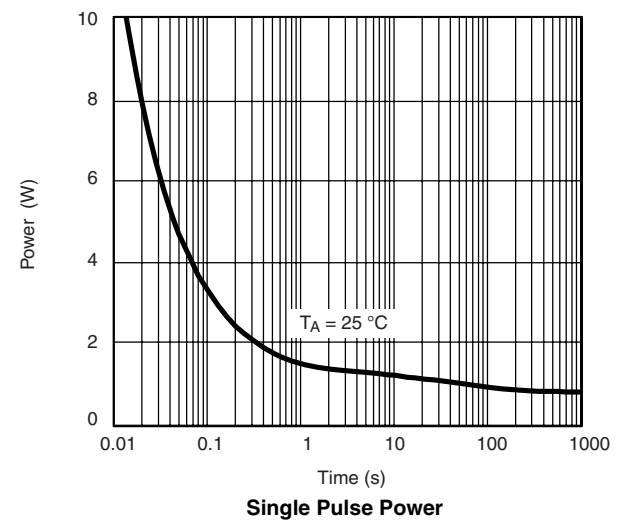
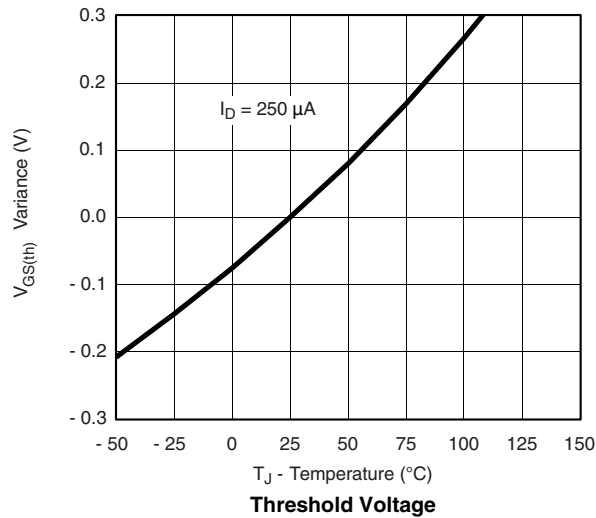
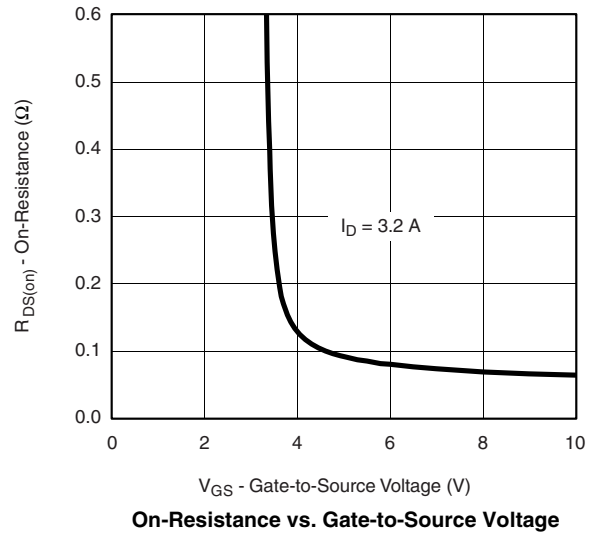
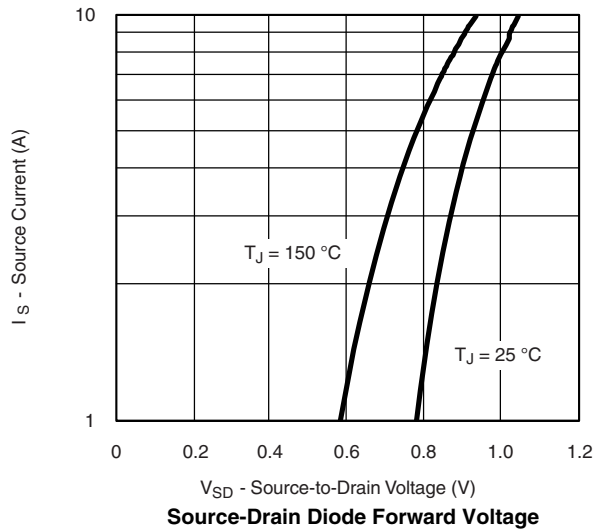
- a. Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. For DESIGN AID ONLY, not subject to production testing.  
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

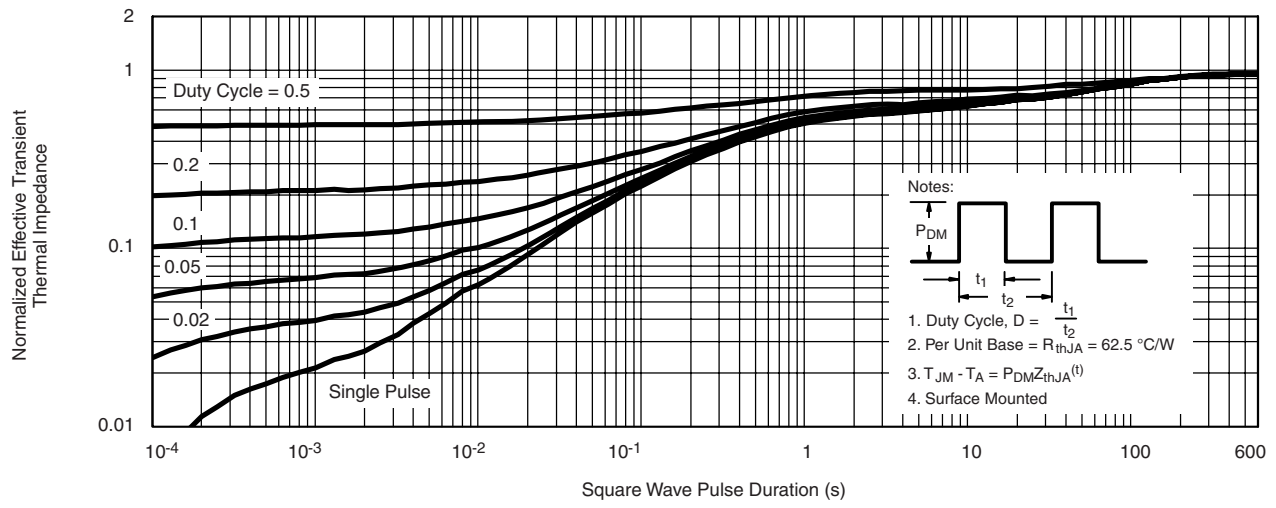


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified  
Square Wave Pulse Duration (s)

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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